

# B.M.S. College of Engineering, Bengaluru-560019

Autonomous Institute Affiliated to VTU

## September / October 2024 Supplementary Examinations

Programme: B.E.

Branch: ES Cluster (EEE/ ECE)

Course Code: 19ES3CCAEC

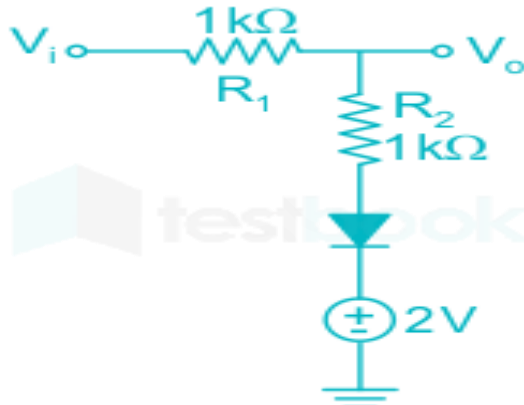
Course: Analog Electronic Circuits

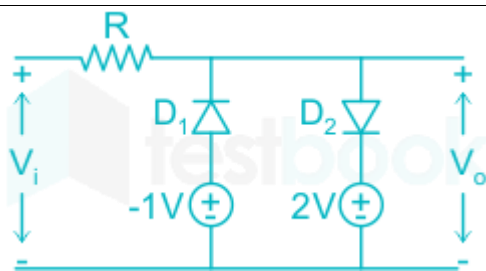
Semester: III

Duration: 3 hrs.

Max Marks: 100

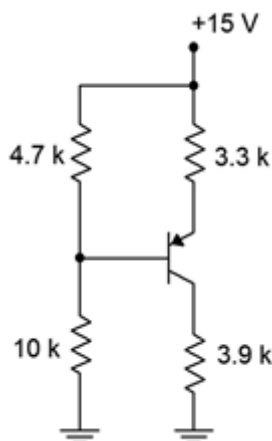
**Instructions:** 1. Answer any FIVE full questions, choosing one full question from each unit.  
2. Missing data, if any, may be suitably assumed.

Important Note: Completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages. Revealing of identification, appeal to evaluator will be treated as			UNIT - I	CO	PO	Marks
	1	a)	Explain the need for Clamping circuits and draw the circuit diagram of positive peak clamper circuit and explain its operation.	CO1	PO1	08
		b)	<p>The diode in the circuit shown in figure 1 has <math>V_{on} = 0.7</math> Volts but is ideal otherwise. If <math>V_i = 5 \sin(\omega t)</math> Volts, the minimum and maximum values of <math>V_o</math> (in Volts) are, respectively,</p>  <p style="text-align: center;"><b>Figure 1</b></p>	CO1	PO1	06
		c)	Derive the equations for current gain, voltage gain, input and output impedance for a Voltage divider configuration using $r_e$ model.	CO1	PO2	06
			<b>OR</b>			
	2	a)	Explain the operation of a negative clipper with neat sketches	CO1	PO1	05
		b)	Two silicon diodes, with a forward voltage drop of 0.7 V, are used in the circuit shown in the figure 2. The range of input voltage $V_i$ for which the output voltage $V_o = V_i$ and Determine the transfer characteristics.	CO1	PO1	07



**Figure 2**

- c) Assuming  $\beta=200$ , determine the Q point ( $I_C$  and  $V_{CE}$ ) for the circuit of Figure 3. Also determine the values of  $V_C$  and  $V_B$ .



**Figure 3**

## UNIT - II

- |   |    |                                                                                                                                                   |     |     |    |
|---|----|---------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|----|
| 3 | a) | Explain the low frequency response of BJT amplifier and derive the expression for $R_i$ , $V_i$ , $R_o$ , $F_{LS}$ , $F_{LE}$ , $R_e$ and $A_v$ . | CO2 | PO1 | 08 |
|   | b) | Prove that Miller effect Capacitance, $C_{\text{miller}} = (1 - A_v)C_f$ .                                                                        | CO2 | PO1 | 07 |
|   | c) | Name any two topologies of the feedback amplifiers and draw any one block diagram schematic among topologies.                                     | CO2 | PO1 | 05 |

## UNIT - III

- |   |    |                                                                                                                                                                               |     |     |    |
|---|----|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|----|
| 4 | a) | For a class B amplifier using a supply of $V_{CC} = 12V$ and driving a load of $8\Omega$ , determine (i) maximum load power (ii) d.c. input power (iii) collector efficiency. | CO3 | PO1 | 07 |
|   | b) | Explain the working of transformer coupled Class A power amplifier with a neat circuit diagram, waveforms and necessary equations.                                            | CO3 | PO2 | 08 |
|   | c) | Define Power Amplifier. Explain the Classification of power amplifiers based on class of operation.                                                                           | CO3 | PO1 | 05 |

## UNIT - IV

- |   |    |                                                                          |     |     |    |
|---|----|--------------------------------------------------------------------------|-----|-----|----|
| 5 | a) | Define Biasing. Explain the different types of biasing MOSFET amplifiers | CO3 | PO1 | 08 |
|   | b) | Draw $V_i$ versus $V_o$ characteristics of n-channel MOSFET.             | CO3 | PO1 | 04 |

	c)	Consider a process technology for which for which $L_{min} = 0.4\mu m$ , $t_{ox} = 8nm$ , $\mu_n = 450cm^2/V.s$ and $V_t = 0.7V$ (i) Find $C_{ox}$ and $k'_n$ (ii) For a MOSFET with $W/L = 8\mu m/0.8\mu m$ , calculate the values of $V_{GS}$ and $V_{DSmin}$ needed to operate the transistor in the saturation region with a dc current $I_D = 100\mu A$ . (iii) For the device in (ii) find the value of $V_{GS}$ required to cause the device to operate as a $1000\Omega$ resistor for a very small $V_{DS}$ .	CO3	PO2	08
		<b>UNIT - V</b>			
6	a)	Explain the working principle of Wilson current mirror and derive an expression for Wilson current transfer ratio.	CO3	PO1	10
	b)	Derive an expression for input resistance, output resistance, voltage gain and overall voltage gain of a common source MOSFET amplifier.	CO3	PO1	10
		<b>OR</b>			
7	a)	Explain the working of current steering circuit using MOSFET with neat Circuit Diagram.	CO4	PO1	10
	b)	Develop a T-equivalent circuit model from its small signal model for an n-channel enhancement MOSFET	CO4	PO1	10

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